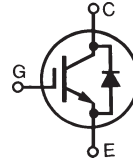


HiPerFAST™ IGBT with Diode C2-Class High Speed IGBTs

IXGR 50N60C2
IXGR 50N60C2D1

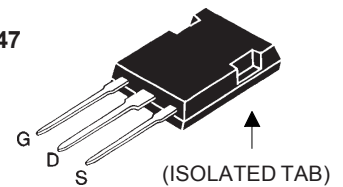
$V_{CES} = 600 \text{ V}$
 $I_{C25} = 75 \text{ A}$
 $V_{CE(sat)} = 2.7 \text{ V}$
 $t_{fi(typ)} = 48 \text{ ns}$

Preliminary Data Sheet



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	75	A
I_{C110}	$T_C = 110^\circ\text{C}$	36	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	300	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 10 \Omega$ Clamped inductive load @ $V_{CE} \leq 600 \text{ V}$	$I_{CM} = 100$	A
P_C	$T_C = 25^\circ\text{C}$	200	W
V_{ISOL}	50/60 Hz RMS, $t = 1 \text{ m}$	2500	V
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Weight		5	g
	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$

ISOPLUS247
(IXGR)



G = Gate C = Collector
E = Emitter

Features

- Very high frequency IGBT and anti-parallel FRED in one package
- Square RBSOA
- High current handling capability
- MOS Gate turn-on for drive simplicity
- Fast Recovery Epitaxial Diode (FRED) with soft recovery and low I_{RM}

Applications

- Switch-mode and resonant-mode power supplies
- Uninterruptible power supplies (UPS)
- DC choppers
- AC motor speed control
- DC servo and robot drives

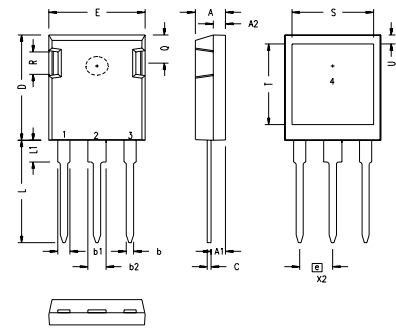
Advantages

- Space savings (two devices in one package)
- Easy to mount with 1 screw

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$			$T_J = 25^\circ\text{C}$: 650 μA $T_J = 125^\circ\text{C}$: 5 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = 40 \text{ A}, V_{GE} = 15 \text{ V}$ Note 1		1.8	$T_J = 25^\circ\text{C}$: 2.7 V $T_J = 125^\circ\text{C}$: V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		Min.	Typ.	Max.	
g_{fs}	$I_C = 40\text{ A}$; $V_{CE} = 10\text{ V}$, Note 1	40	51	S	
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		3700	pF	
C_{oes}			290	pF	
C_{res}			50	pF	
Q_g	$I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		138	nC	
Q_{ge}			25	nC	
Q_{gc}			40	nC	
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 480\text{ V}$, $R_G = R_{off} = 2.0\ \Omega$		18	ns	
t_{ri}			25	ns	
$t_{d(off)}$			115	150	ns
t_{fi}			48		ns
E_{off}			0.38	0.7	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 480\text{ V}$, $R_G = R_{off} = 2.0\ \Omega$		18	ns	
t_{ri}			25	ns	
E_{on}			1.4	mJ	
$t_{d(off)}$			170	ns	
t_{fi}			60	ns	
E_{off}		0.74	mJ		
R_{thJC}			0.62	K/W	
R_{thCK}		0.15		K/W	

ISOPLUS 247 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

Reverse Diode (FRED)

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = 60\text{ A}$, $V_{GE} = 0\text{ V}$, Note 1 $T_J = 150^\circ\text{C}$			2.1 V 1.4
I_{RM}	$I_F = 60\text{ A}$, $V_{GE} = 0\text{ V}$, $-di_F/dt = 100\text{ A}/\mu$ $V_R = 100\text{ V}$ $T_J = 100^\circ\text{C}$			8.3 A
t_{rr}	$I_F = 1\text{ A}$; $-di/dt = 200\text{ A/ms}$; $V_R = 30\text{ V}$		35	ns
R_{thJC}				0.85 K/W

Note 1: Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343	6,583,505
	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344

Fig. 1. Output Characteristics @ 25 Deg. C

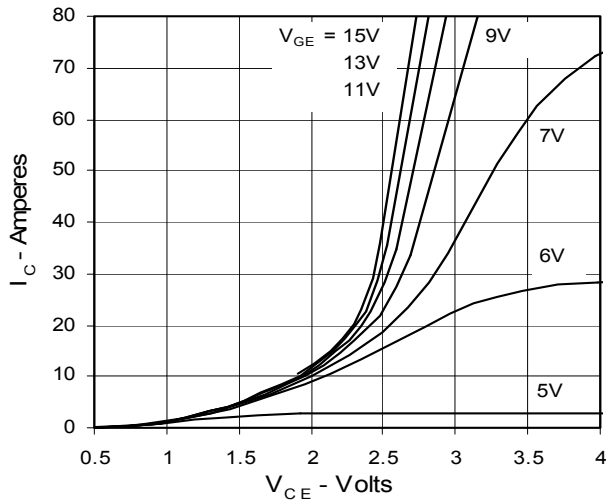


Fig. 2. Extended Output Characteristics @ 25 deg. C

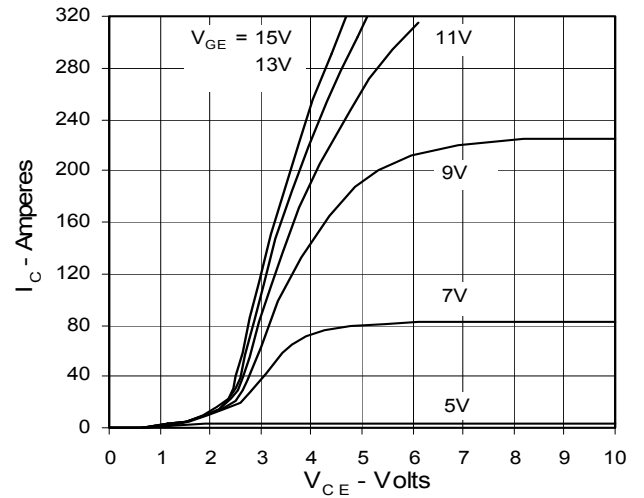


Fig. 3. Output Characteristics @ 125 Deg. C

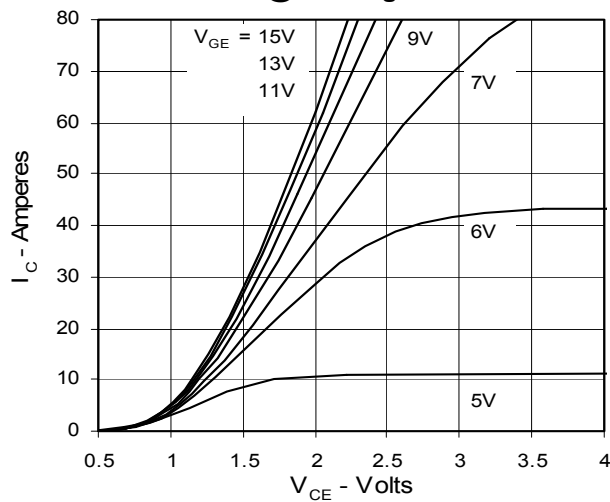


Fig. 4. Dependence of $V_{CE(sat)}$ on Temperature

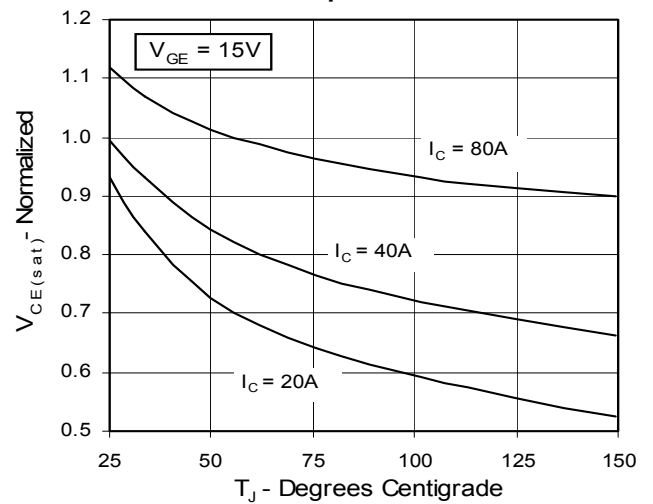


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter voltage

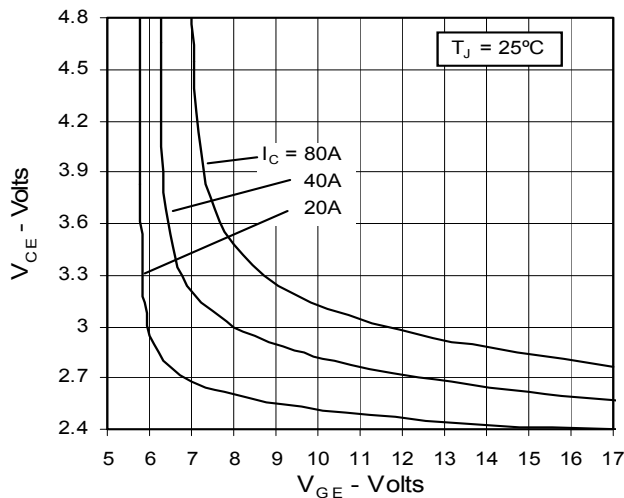


Fig. 6. Input Admittance

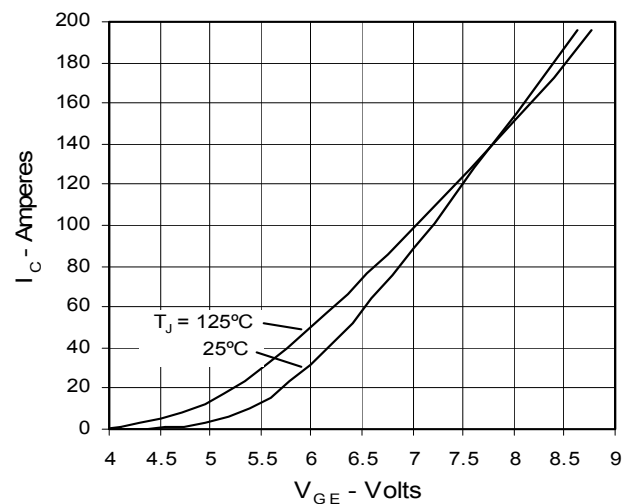


Fig. 7. Transconductance

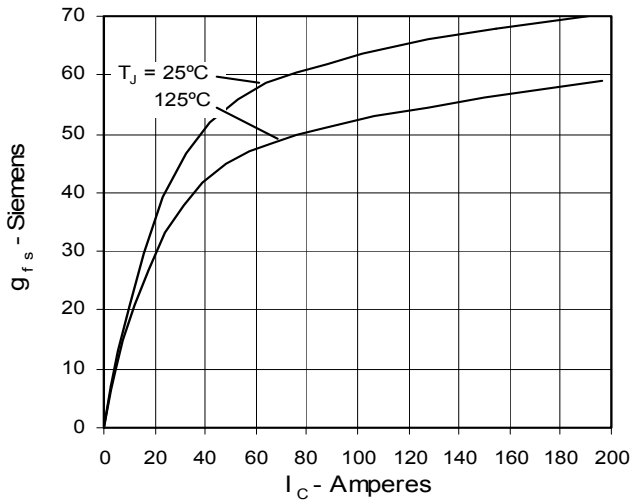


Fig. 8. Dependence of Turn-Off Energy on R_G

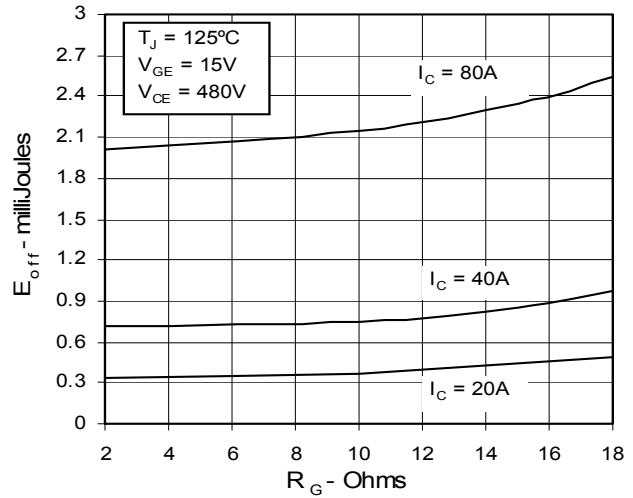


Fig. 9. Dependence of Turn-Off Energy on I_c

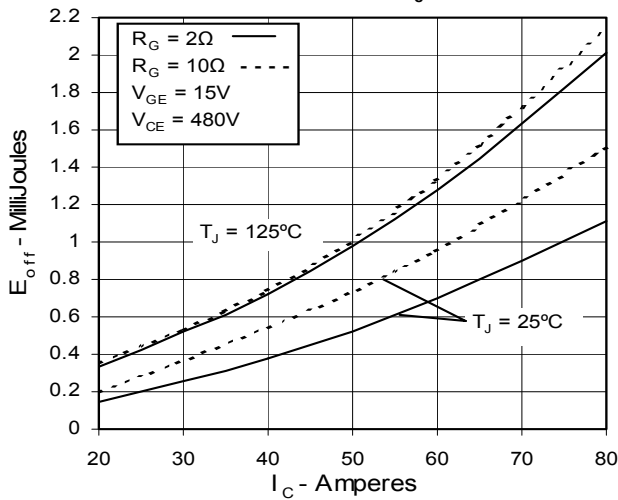


Fig. 10. Dependence of Turn-Off Energy on Temperature

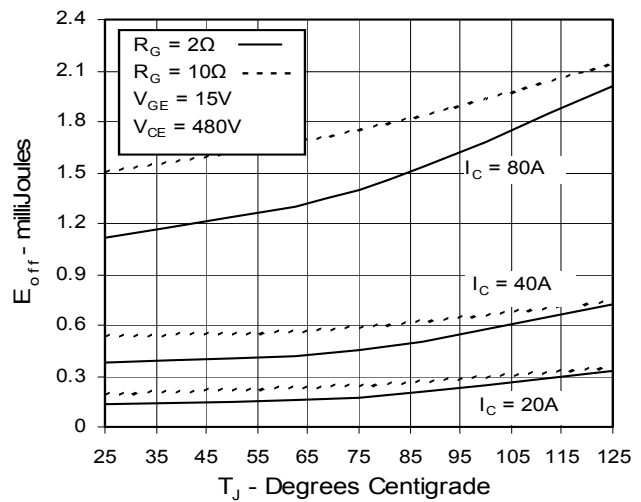


Fig. 11. Dependence of Turn-Off Switching Time on R_G

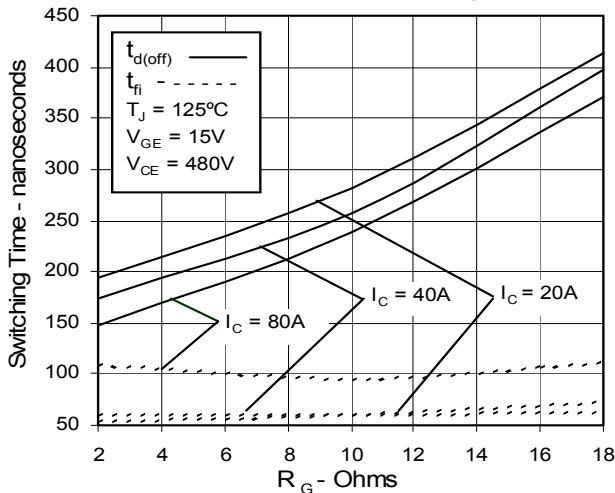
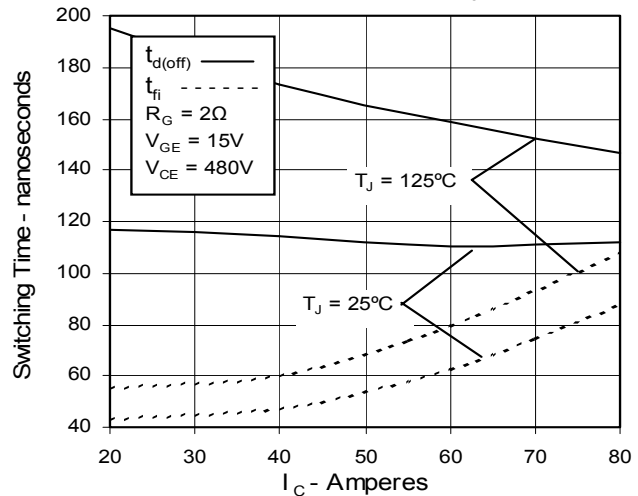


Fig. 12. Dependence of Turn-Off Switching Time on I_c



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4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344

Fig. 13. Dependence of Turn-Off Switching Time on Temperature

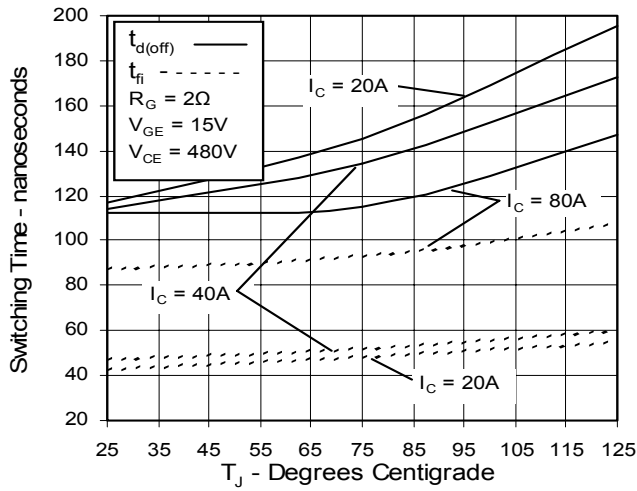


Fig. 14. Reverse-Bias Safe Operating Area

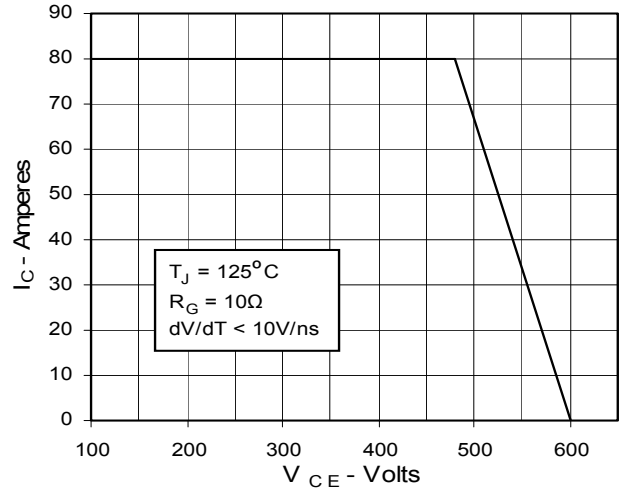


Fig. 15. Gate Charge

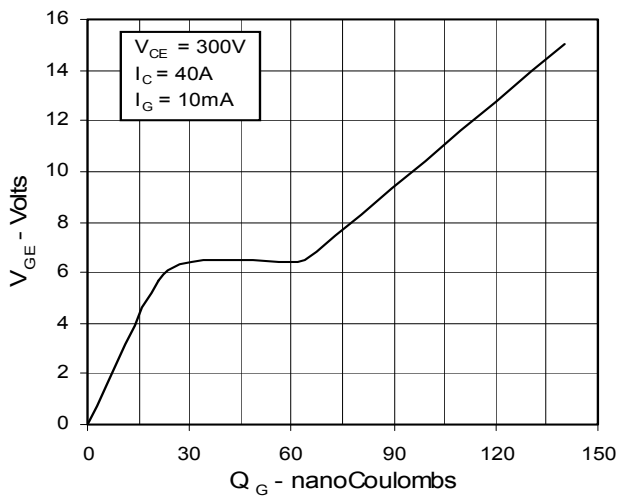


Fig. 16. Capacitance

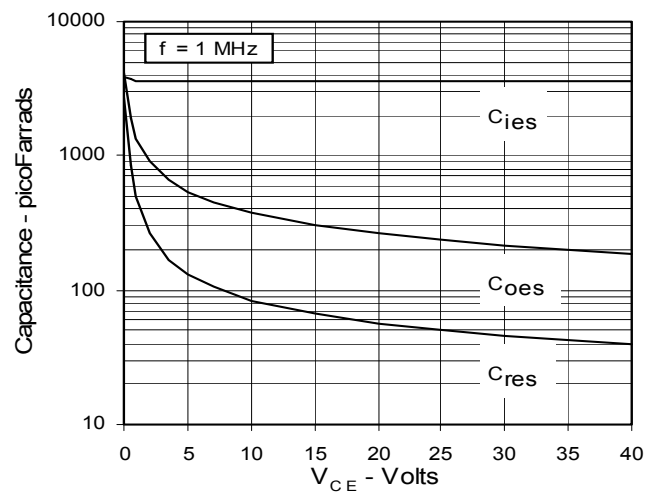
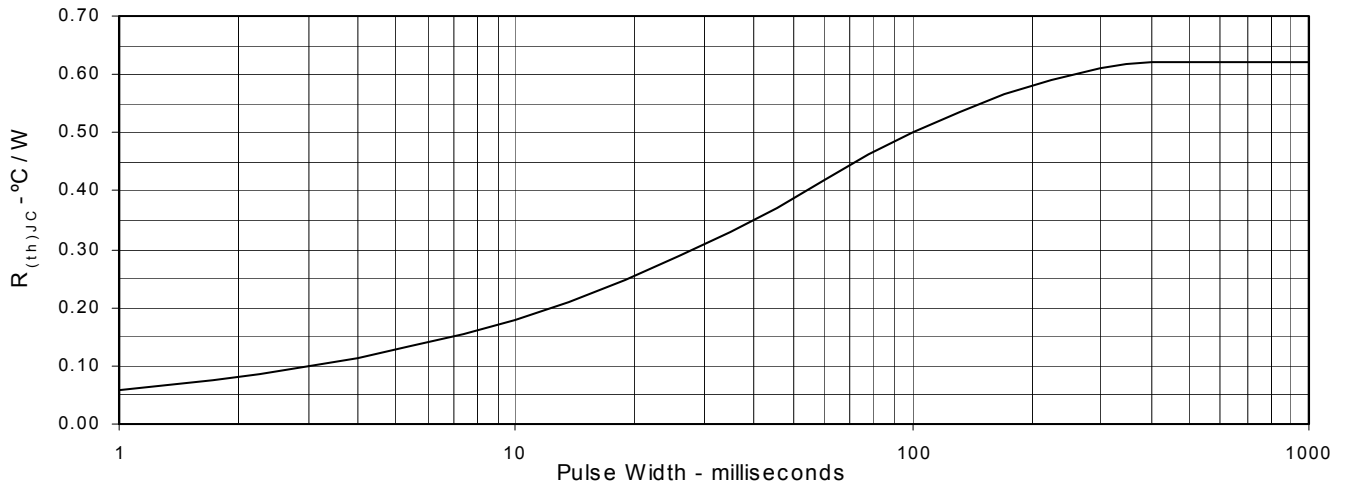


Fig. 16. Maximum Transient Thermal Resistance



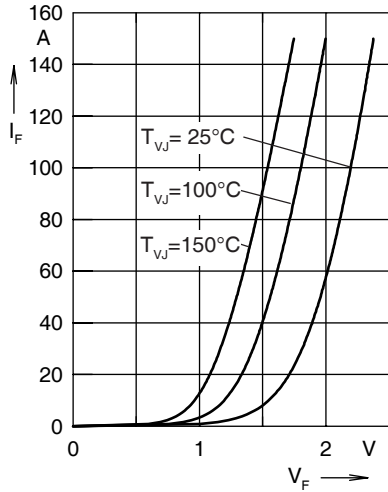


Fig. 18 Forward current I_F versus V_F

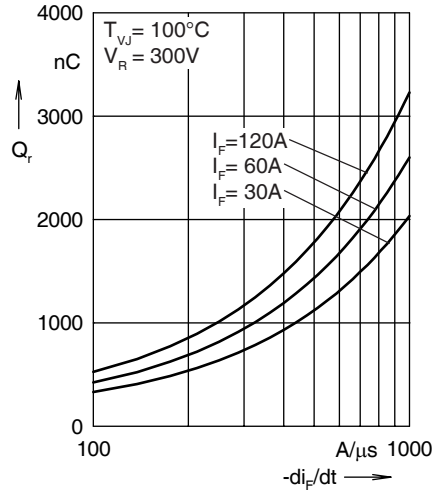


Fig. 19 Reverse recovery charge Q_r versus $-di_F/dt$

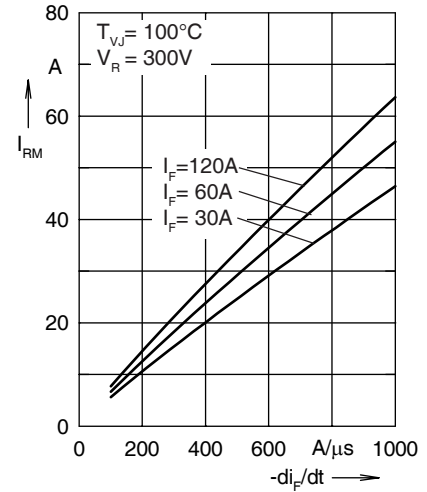


Fig. 20 Peak reverse current I_{RM} versus $-di_F/dt$

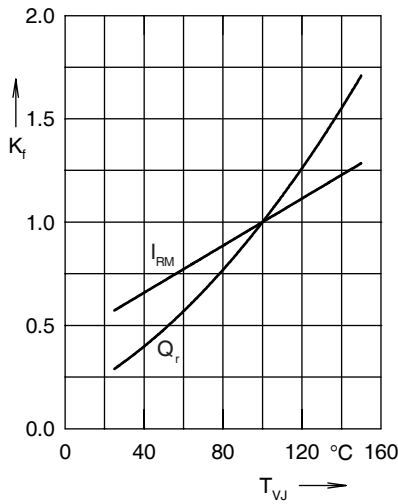


Fig. 21 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

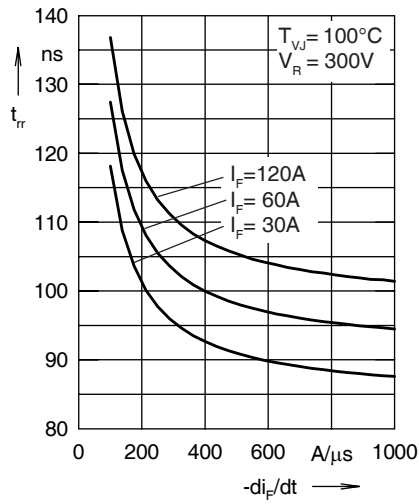


Fig. 22 Recovery time t_{rr} versus $-di_F/dt$

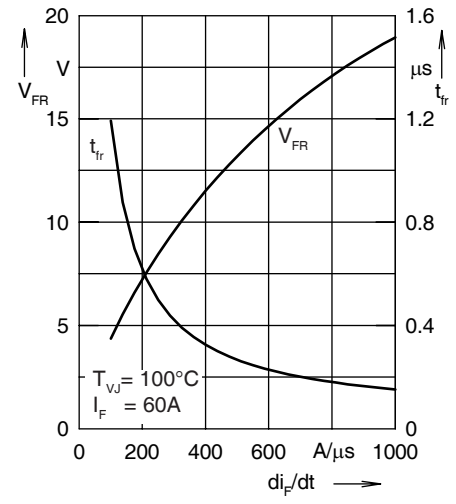


Fig. 23 Peak forward voltage V_{FR} and t_{tr} versus di_F/dt

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.3073	0.0055
2	0.3533	0.0092
3	0.0887	0.0007
4	0.1008	0.0399

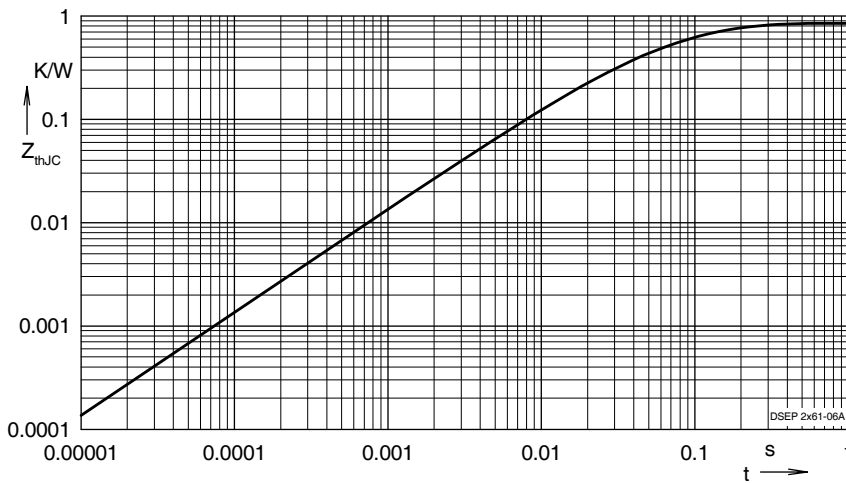


Fig. 24 Transient thermal resistance junction to case

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4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1 6,683,344